# 2.5V Drive Nch MOS FET RTF015N03

#### Structure

Silicon N-channel MOS FET

### ● Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TUMT3).
- 3) Low voltage drive (2.5V drive).

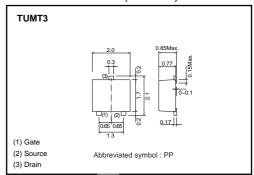
# Applications

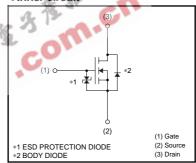
Switching

#### Packaging specifications

	Package	Taping
Type	Code	TL
	Basic ordering unit (pieces)	3000
RTF015N03	0	

# ●External dimensions (Unit : mm)





### ● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		VDSS	30	V
Gate-source voltage		Vgss	12	V
Drain augrant	Continuous	lσ	±1.5	Α
Drain current	Pulsed	IDP *1	±6.0	Α
Source current	Continuous	Is	0.6	Α
(Body diode)	Pulsed	Isp *1	6.0	А
Total power dissipation		P <sub>D</sub> *2	0.8	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C
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<sup>\*1</sup> Pw≤10μs, Duty cycle≤1% \*2 Mounted on a ceramic board

### ●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	156	°C/W

<sup>\*</sup> Mounted on a ceramic board

# ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	-	10	μΑ	Vgs=12V, Vps=0V
Drain-source breakdown voltage	$V_{(BR)\;DSS}$	30	_	_	V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	-	_	1	μΑ	V <sub>DS</sub> = 30V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	0.5	_	1.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Static drain-source on-state resistance		_	170	240	mΩ	I <sub>D</sub> = 1.5A, V <sub>GS</sub> = 4.5V
	R <sub>DS (on)</sub> *	_	180	250	mΩ	I <sub>D</sub> = 1.5A, V <sub>GS</sub> = 4V
		-	240	340	mΩ	I <sub>D</sub> = 1.5A, V <sub>GS</sub> = 2.5V
Forward transfer admittance	Y <sub>fs</sub>   *	1.5	_	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1.5A
Input capacitance	Ciss	_	80	_	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss	_	14	_	pF	Vgs=0V
Reverse transfer capacitance	Crss	_	12	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	_	7	_	ns	V <sub>DD</sub> ≒ 15V
Rise time	tr *	-	9	_	ns	I <sub>D</sub> = 0.75A V <sub>G</sub> s= 4.5V
Turn-off delay time	td (off) *	_	15	_	ns	$R_L=20\Omega$
Fall time	t <sub>f</sub> *	-	6	_	ns	R <sub>G</sub> =10Ω
Total gate charge	Qg *	-	1.6	2.2	nC	V <sub>DD</sub> = 15V V <sub>GS</sub> = 4.5V
Gate-source charge	Q <sub>gs</sub> *	-	0.5	_	nC	I <sub>D</sub> = 1.5A
Gate-drain charge	Q <sub>gd</sub> *	_	0.3	_	nC	RL=10Ω RG=10Ω

\*Pulsed

# ●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp	_	_	1.2	✓ V	s= 0.6A, V <sub>GS</sub> = <b>0</b> V

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